

SCHOTTKY BARRIER RECTIFIER

FEATURES

- ◇ Metal-semiconductor junction with guard ring
- ◇ Epitaxial construction
- ◇ Low forward voltage drop, low switching losses
- ◇ High surge capability
- ◇ For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- ◇ The plastic material carries U/L recognition 94V-0

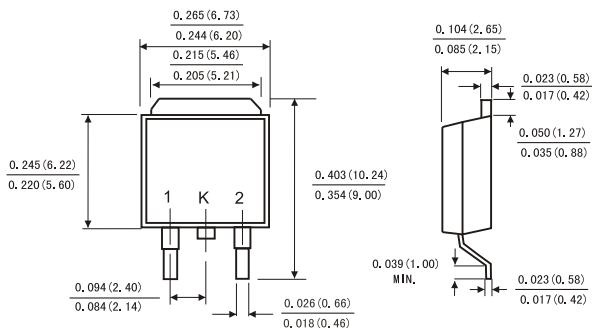
MECHANICAL DATA

- ◇ Case: JEDEC TO-252AC, molded plastic
- ◇ Terminals: Axial lead, solderable per MIL-STD-202, Method 208
- ◇ Polarity: As marked
- ◇ Weight: 0.014 ounces, 0.4 grams
- ◇ Mounting position: Any

VOLTAGE RANGE: 20 --- 200 V
CURRENT: 6.0A

TO - 252AC

(DPAK)



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

	Symbols	MBR 620	MBR 630	MBR 640	MBR 650	MBR 660	MBR 680	MBR 6A0	MBR 6150	MBR 6200	Units					
Maximum repetitive peak reverse voltage	V _{RRM}	20	30	40	50	60	80	100	150	200	Volts					
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	57	71	105	140	Volts					
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	150	200	Volts					
Maximum average forward rectified current 0.375"(9.5mm) lead length(see fig.1)	I _(AV)	6.0								Amps						
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method at rated T _J)	I _{FSM}	150.0								Amps						
Maximum instantaneous forward voltage at 6.0 A(Note 1)	V _F	0.60		0.75		0.85		0.90		0.95						
Maximum instantaneous reverse current at rated DC blocking voltage(Note 1)	I _R	T _A = 25°C	0.2								mA					
		T _A = 100°C	50		25											
Typical junction capacitance(Note 3)	C _J	500		400												
Typical thermal resistance (Note 2)	R _{θJA} R _{θJL}	25.0 8.0								°C/W						
Operating junction temperature range	T _J	-65 to +150								°C						
Storage temperature range	T _{STG}	-65 to +150								°C						

NOTE: 1. Pulse test: 300us pulse width, 1% duty cycle.

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2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

3. Thermal resistance junction to ambient

RATINGS AND CHARACTERISTIC CURVES

MBR620 --- MBR6200

FIG.1-FORWARD CURRENT DERATING CURVE

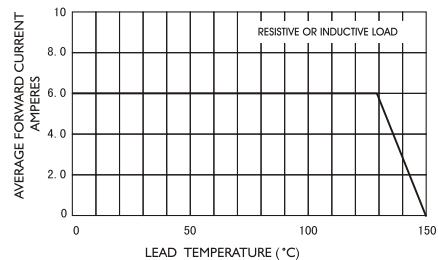


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

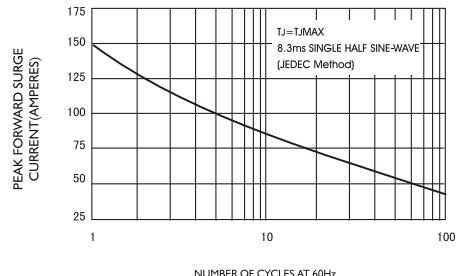


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

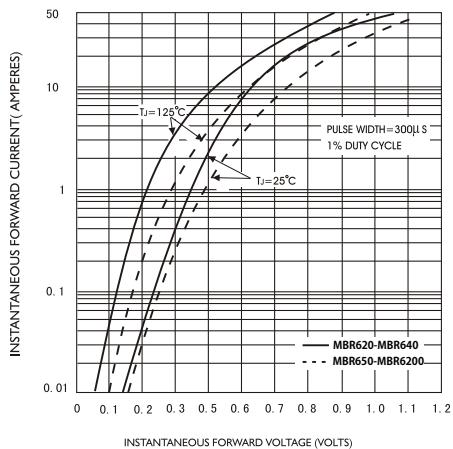


FIG.4-TYPICAL REVERSE CHARACTERISTICS

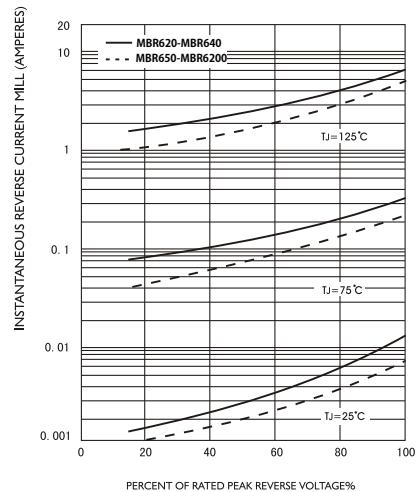


FIG.5-TYPICAL JUNCTION CAPACITANCE

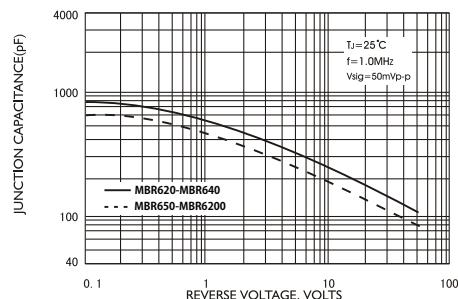


FIG.6-TYPICAL TRANSIENT THERMAL IMPEDANCE

